IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony et al.

Docket:

TI-24953

Serial No.:

09/116.138

Examiner:

W. D. Coleman

Filed:

07/15/98

Art Unit:

2823

For:

High Permittivity Silicate Gate Dielectric

REPLY PURSUANT TO 37 C.F.R. § 1.111

April 14, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

FACSIMILE CERTIFICATE I bereby certify that this correspondence is being transmitted by Facsimile to the Patent and Trademark Office in accordance with 37 C.F.R. §1.6d on April 23, 2004.

Examiner:

In response to the Office Action dated December 16, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS

Please rejoin claims 28, 29, 46, 71, 72, and 73.

122/2004 R.W. 115 FC:125

B. Please replace the claims with the claims on the following sheets.

Claims 1 and 46 are amended below.

Withdrawn claims 2 - 25, 36 - 40, 47 - 70, and 74 - 80 are canceled below.

Claims 31 - 35 and 41 - 45 were canceled in a previous amendment.

With the rejoinder requested above, this leaves claims 1, 26 - 30, 46, and 71 - 73 active.

(Currently amended) A method of fabricating a field-effect transistor device on an 1. integrated circuit, comprising the steps of: providing a single-crystal silicon substrate; forming a metal silicate dielectric layer on the substrate; and

forming a conductive transistor gate overlying the metal silicate dielectric layer.

REMARKS

- Claims 1 and 46 are amended per the agreement at the interview. Previously withdrawn 1. claims 2 - 25, 36 - 40, 47 - 70, and 74 - 80 are canceled. If the linking claims are allowed, Applicants intend to present most of these canceled claims in a future amendment per the procedure outlined in MPEP §809.04. With the rejoinder requested above, this leaves claims 1, 26 - 30, 46, and 71 - 73 active.
- Claims 1 and 46 are now clearly limited to methods of fabricating field-effect transistors. 2. Hsieh '035 does not teach or suggest the clarified claims.
- Applicant respectfully petitions the Commissioner for a two month extension of the 3. shortened statutory period for response in the above-identified application. Please charge this and any other required fee-including additional extension of time fees-to the deposit account of Texas Instruments Incorporated, Account No. 20-0668. Any further necessary extension of time is hereby requested.
- Applicant believes that the application is in condition for allowance. If Examiner has any 4. further comments or suggestions, Applicant respectfully requests that Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

Respectfully submitted,

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